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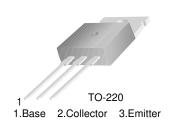
July 2008

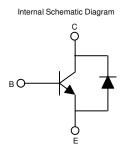
## **FJP3307D**

## **High Voltage Fast Switching NPN Power Transistor**

### **Features**

- · Built-in Diode between Collector and Emitter
- · Suitable for Electronic Ballast and Switch Mode Power Supplies





### **Absolute Maximum Ratings**

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	700	V
V <sub>CEO</sub>	Collector-Emitter Voltage	400	V
V <sub>EBO</sub>	Emitter-Base Voltage	9	V
I <sub>C</sub>	Collector Current (DC)	8	А
I <sub>CP</sub>	* Collector Current (Pulse)	16	А
I <sub>B</sub>	Base Current (DC)	4	A
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> = 25°C)	80	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

<sup>\*</sup> Pulse Test: PW = 300ms, Duty Cycle = 2% Pulsed

### Electrical Characteristics T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Тур.	Max	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 500 \mu A, I_E = 0$	700			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_{C} = 5mA, I_{B} = 0$	400			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 500 \mu A, I_C = 0$	9			V
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = 9V, I_{C} = 0$			1	mA
h <sub>FE1</sub> h <sub>FE2</sub>	DC Current Gain	$V_{CE} = 5V, I_{C} = 2A$ $V_{CE} = 5V, I_{C} = 5A$	8 5		40 30	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_C = 2A, I_B = 0.4A$			1	V
		I <sub>C</sub> = 5A, I <sub>B</sub> = 1A			2	V
		I <sub>C</sub> = 8A, I <sub>B</sub> = 2A			3	V

Symbol	Parameter	Conditions	Min.	Тур.	Max	Units
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	$I_C = 2A, I_B = 0.4A$			1.2	V
		I <sub>C</sub> = 5A, I <sub>B</sub> = 1A			1.6	V
V <sub>F</sub>	Diode Forward Voltage	I <sub>C</sub> = 3A			2.5	V
C <sub>ob</sub>	Output Capatitance	V <sub>CB</sub> = 10V, I <sub>E</sub> = 0, f = 1MHz		60		pF
t <sub>STG</sub>	Storage Time	$V_{CC} = 125V, I_C = 5A$ $I_{B1} = -I_{B2} = 1A, R_L = 50\Omega$			3	μS
t <sub>F</sub>	Fall Time				0.7	μS
t <sub>STG</sub>	Storage Time	$V_{CC} = 30V, I_C = 5A, L=200\mu H$			2.3	μS
t <sub>F</sub>	Fall Time	$I_{B1}$ =1A, $R_{BB}$ = 0 $\Omega$ , $V_{BE(OFF)}$ = -5 $V$ $V_{CLAMP}$ = 250 $V$			150	ns

<sup>\*</sup> Pulse test:  $PW=300\mu s,~Duty~cycl~e=2\%$ 

## $\mathbf{h}_{\text{FE}}$ Classification

Classification	H1	H2
h <sub>FE1</sub>	15 ~ 28	26 ~ 39

## **Typical Characteristics**

Figure 1. Static Characterstic

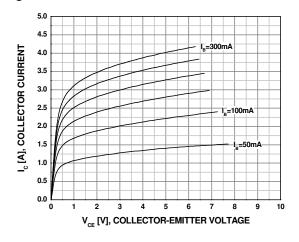


Figure 2. DC Current Gain (H1 Grade)

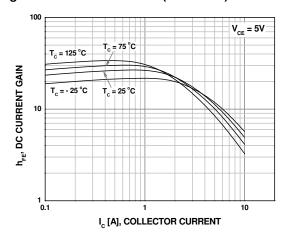


Figure 3. DC Current Gain (H2 Grade)

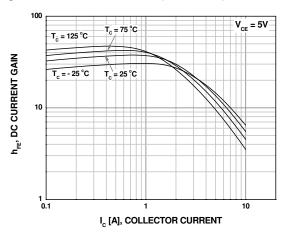


Figure 4. Collector-Emitter Saturation Voltage

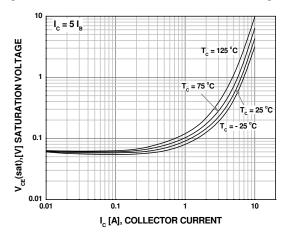


Figure 5. Base-Emitter Saturation Voltage

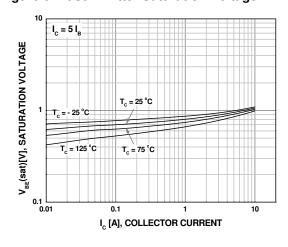
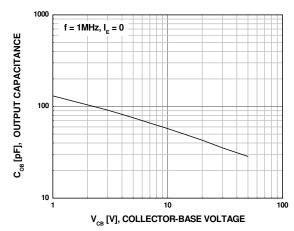


Figure 6. Output Capacitance



## **Typical Characteristics** (Continued)

Figure 7. Power Derating

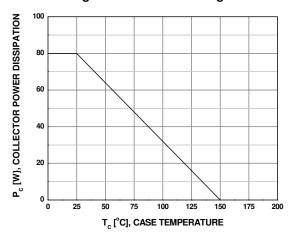


Figure 8. Reverse Biased Safe Operating Area

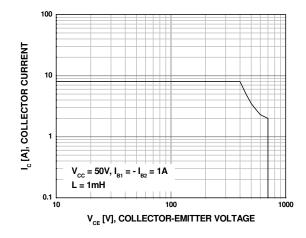
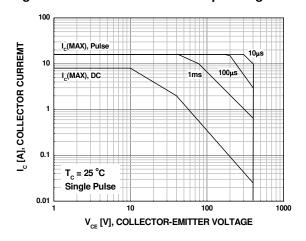
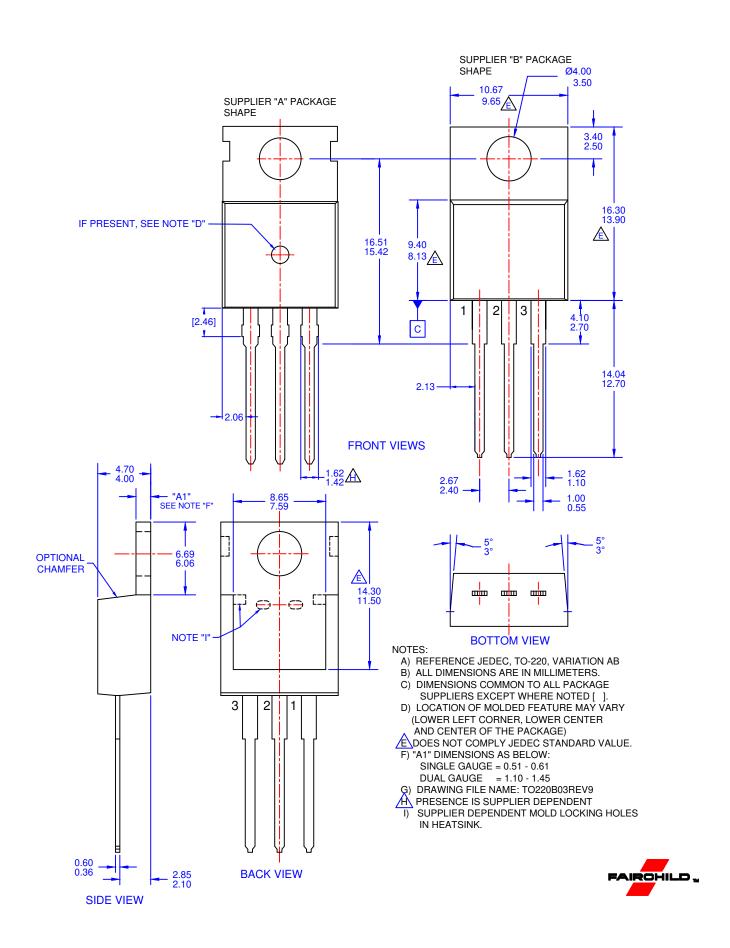


Figure 9. Forward Biased Safe Operating Area





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